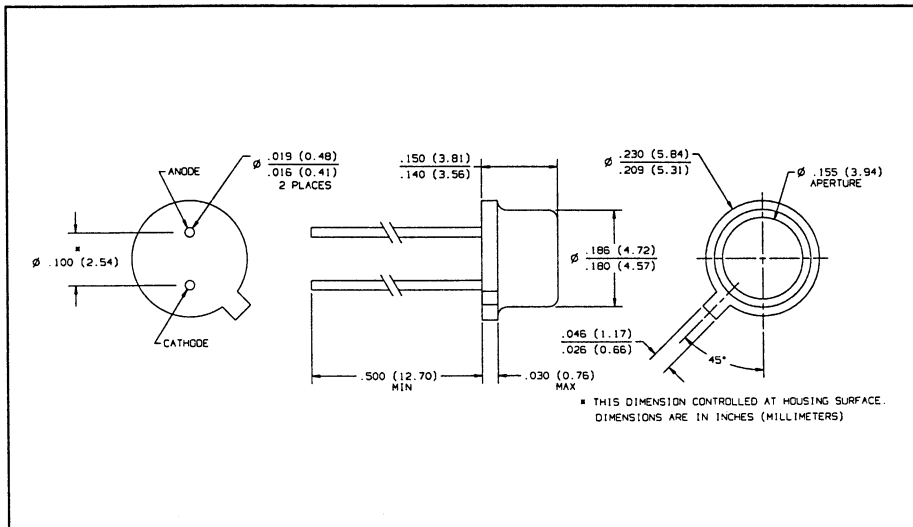
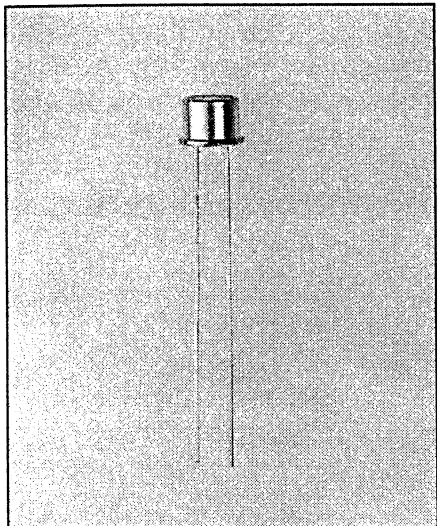


GaAlAs Hermetic Infrared Emitting Diodes

Types OP231W, OP232W, OP233W



Features

- Wide irradiance pattern
- Enhanced temperature range
- Mechanically and spectrally matched to the OP800WSL and OP830SL series devices
- Significantly higher power output than GaAs at equivalent drive currents
- TO-46 hermetically sealed package

Description

The OP231W series devices are 890nm gallium aluminum arsenide infrared emitting diodes mounted in hermetically sealed packages. The broad irradiance pattern provides relatively even illumination over a large area.

Replaces

K6300 series

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Reverse Voltage	2.0 V
Continuous Forward Current	100 mA
Peak Forward Current (2 μs pulse width, 0.1% duty cycle)	10.0 A
Storage Temperature Range	-65°C to $+150^\circ\text{C}$
Operating Temperature Range	-65°C to $+125^\circ\text{C}$
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 sec. with soldering iron]	260°C ⁽¹⁾
Power Dissipation	200 mW ⁽²⁾

Notes:

- (1) RMA flux is recommended. Duration can be extended to 10 seconds max. when flow soldering.
- (2) Derate linearly 2.0 mW/ $^\circ\text{C}$ above 25°C .
- (3) $E_{e(\text{APT})}$ is a measurement of the average radiant intensity within the cone formed by the measurement surface, a radius of 0.466" (11.84 mm) measured from the lens side of the tab to the sensing surface, and a sensing surface of 0.250" (6.35 mm) in diameter forming a 30° cone. $E_{e(\text{APT})}$ is not necessarily uniform within the measured area.
- (4) Measurement made with 100 μs pulse measured at the trailing edge of the pulse with a duty cycle of 0.1% and an $I_F = 100\text{ mA}$.

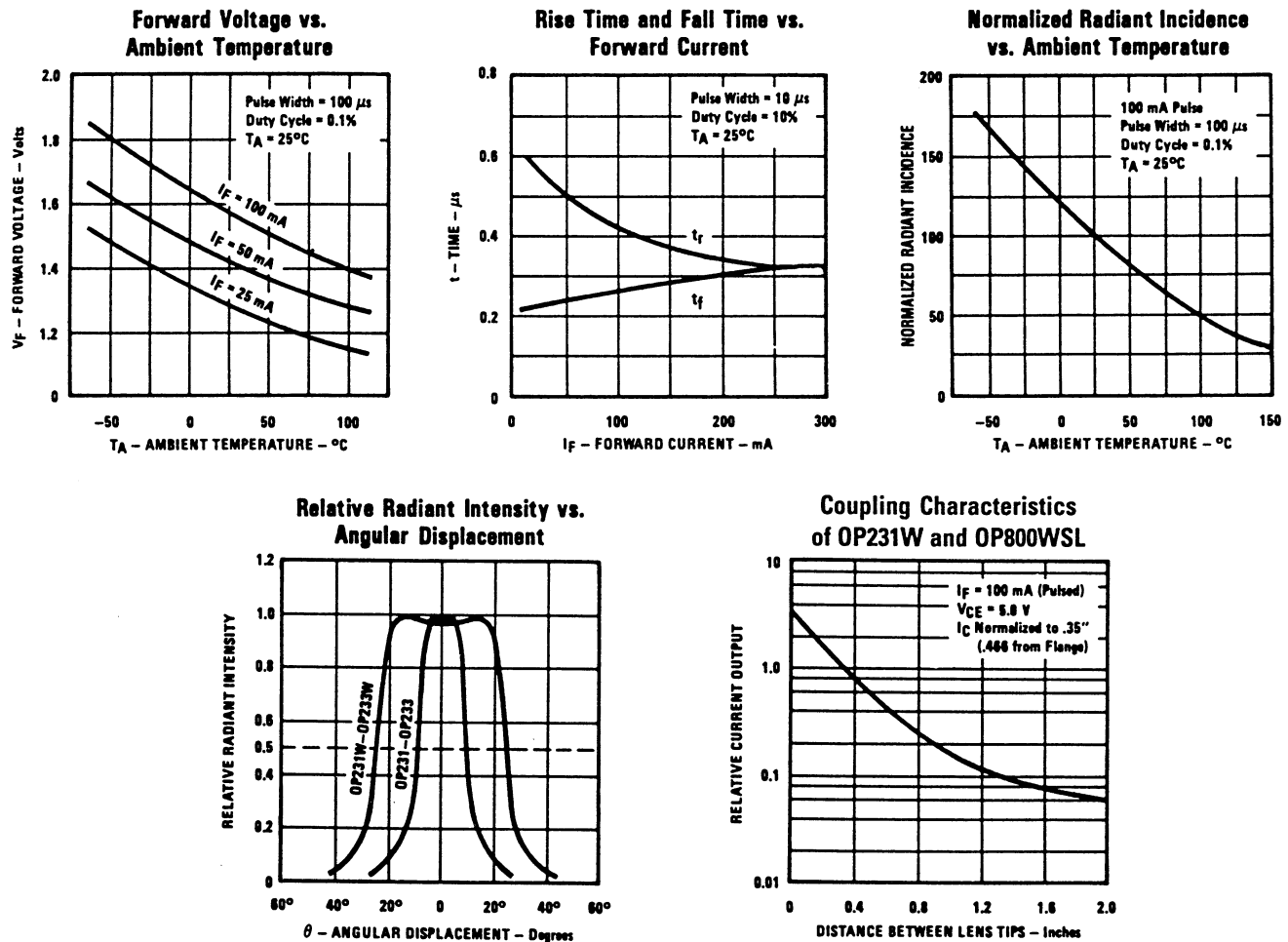
Types OP231W, OP232W, OP233W

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
$E_e(\text{APT})$	Apertured Radiant Incidence	OP231W OP232W OP233W	1.5 3.5 5.0		mW/cm^2 mW/cm^2 mW/cm^2	$I_F = 100\text{ mA}^{(3)(4)}$ $I_F = 100\text{ mA}^{(3)(4)}$ $I_F = 100\text{ mA}^{(3)(4)}$
V_F	Forward Voltage			2.0	V	$I_F = 100\text{ mA}^{(4)}$
I_R	Reverse Current			100	μA	$V_R = 2.0\text{ V}$
λ_p	Wavelength at Peak Emission		890		nm	$I_F = 10\text{ mA}$
B	Spectral Bandwidth Half Power Points		80		nm	$I_F = 10\text{ mA}$
$\Delta\lambda_p/\Delta T$	Spectral Shift with Temperature		+0.30		$\text{nm}/^\circ\text{C}$	$I_F = \text{Constant}$
θ_{HP}	Emission Angle at Half Power Points		50		Deg.	$I_F = 100\text{ mA}$
t_r	Output Rise Time		500		ns	$I_F(\text{PK}) = 100\text{ mA}$, $\text{PW} = 10\text{ }\mu\text{s}$, D.C. = 10%
t_f	Output Fall Time		250		ns	$I_F(\text{PK}) = 100\text{ mA}$, $\text{PW} = 10\text{ }\mu\text{s}$, D.C. = 10%

INFRARED
EMITTING
DIODES

Typical Performance Curves



Optek reserves the right to make changes at any time in order to improve design and to supply the best product possible.

Optek Technology, Inc. 1215 W. Crosby Road Carrollton, Texas 75006 (972)323-2200 Fax (972)323-2396